

a first current blocking layer formed on said flat portion and on sidewalls of said ridge portion of said cladding layer and composed of a high-resistive nitride based semiconductor containing impurities;

Cancelled A1
wherein the cladding layer is composed of AlGaN; and

wherein the first current blocking layer is composed of AlGaN having a larger Al composition ratio than that of the cladding layer.

10. (Amended) A semiconductor light emitting device comprising:

an active layer composed of a nitride based semiconductor;

A2
a cladding layer formed on said active layer, composed of a nitride based semiconductor of a first conductivity type, and having a flat portion and a ridge portion formed on the flat portion, said cladding layer having a recess on said flat portion along both sidewalls of said ridge portion; and

a first current blocking layer formed on said flat portion and on the sidewalls of said ridge portion such that it is embedded in said recess of said cladding layer;

wherein the cladding layer is composed of AlGaN; and

wherein the first current blocking layer is composed of AlGaN having a larger Al composition ratio than that of the cladding layer.
